MOSFET - Dual, P-Channel, Small Signal, XLLGAS6, 0.65mm x 0.90mm x 0.4mm

-20 V, -127 mA

Features

- Dual P-Channel MOSFET
- Offers a Low $R_{DS(ON)}$ Solution in the Ultra Small 0.65 mm \times 0.90 mm Package
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Small Signal Load Switch
- Analog Switch
- High Speed Interfacing
- Optimized for Power Management in Ultra Portable Products

MAXIMUM RATINGS (T_J = 25°C unless otherwise specified)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	-20	V
Gate-to-Source Voltage			V _{GS}	±8	V
Continuous Drain	Steady	T _A = 25°C	I _D	-127	mA
Current (Note 1)	State	T _A = 85°C		-91	
	t ≤ 5 s	T _A = 25°C		-146	
Power Dissipation (Note 1)	Steady State	T _A = 25°C	P _D	125	mW
	t ≤ 5 s			166	
Pulsed Drain Current $t_p = 10 \mu s$			I _{DM}	-488	mA
Operating Junction and Storage Temperature			T _J , T _{STG}	–55 to 150	°C
Source Current (Body Diode) (Note 2)			Is	-200	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			TL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.
- 2. Pulse Test: pulse width \leq 300 μ s, duty cycle \leq 2%

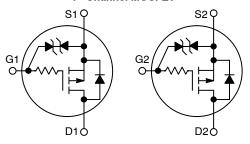


ON Semiconductor®

www.onsemi.com

V _{(BR)DSS}	R _{DS(ON)} MAX	I _D Max
-20 V	5.0 Ω @ -4.5 V	
	6.0 Ω @ -2.5 V	–127 mA
	7.0 Ω @ –1.8 V	-127 IIIA
	10.0 Ω @ -1.5 V	

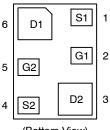
P-Channel MOSFET





XLLGA6 Case 713AC

PINOUT DIAGRAM



(Bottom View)

MARKING DIAGRAM



K = Specific Device Code M = Date Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient (Note 3) Steady State t ≤ 5 s	$R_{ hetaJA}$	998 751	°C/W

^{3.} Surface-mounted on FR4 board using the minimum recommended pad size, 1 oz Cu.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS				U .	u.		
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$		-20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V,	T _J = 25°C			-50	nA
		$V_{DS} = -5 V$	T _J = 85°C			-200	nΑ
		V _{GS} = 0 V, V _{DS} = -16 V	T _J = 25°C			-100	
Gate-to-Source Leakage Current	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 5.0 \text{ V}$				±100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_D = -250 \mu A$		-0.4		-1.0	V
Drain-to-Source On Resistance	R _{DS(ON)}	$R_{DS(ON)}$ $V_{GS} = -4.5 \text{ V, } I_D = -100 \text{ mA}$			2.1	5.0	Ω
		V_{GS} = -2.5 V, I_D = -50 mA			2.7	6.0	
		$V_{GS} = -1.8 \text{ V}, I_D = -20 \text{ mA}$			3.4	7.0	
		$V_{GS} = -1.5 \text{ V}, I_D = -10 \text{ mA}$			4.2	10.0	
Forward Transconductance	9FS	V _{DS} = -5.0 V, I _D = -125 mA			0.35		S
Forward Diode Voltage	V _{SD}	$V_{GS} = 0 \text{ V, } I_{S} = -10 \text{ mA}$			-0.6	-1.0	V
CAPACITANCES							
Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz	, V _{DS} = -15 V		12.8		pF
Output Capacitance	C _{OSS}				2.8		
Reverse Transfer Capacitance	C _{RSS}				2.0		
SWITCHING CHARACTERISTICS, V _{GS} =	4.5 V			•			
Turn-On Delay Time	t _{d(ON)}	V_{GS} = -4.5 V, V_{DD} = -15 V, I_D = -200 mA, R_G = 2.0 Ω			37		ns
Rise Time	t _r				71		
Turn-Off Delay Time	t _{d(OFF)}				280		
Fall Time	t _f				171		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Package	Shipping [†]
NTND31211PZTAG	XLLGA6 (Pb-Free)	8000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

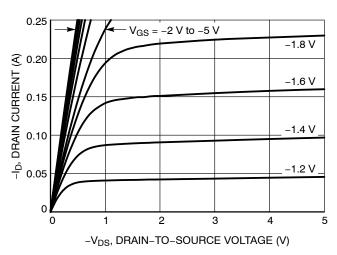
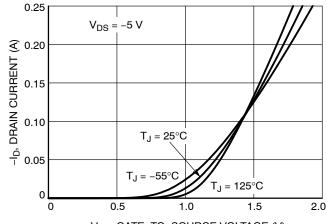


Figure 1. On-Region Characteristics



-V_{GS}, GATE-TO-SOURCE VOLTAGE (V) Figure 2. Transfer Characteristics

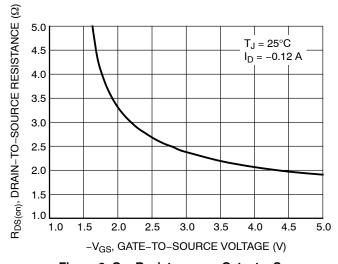


Figure 3. On-Resistance vs. Gate-to-Source Voltage

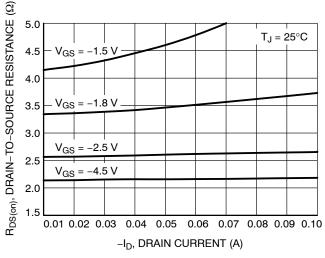


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

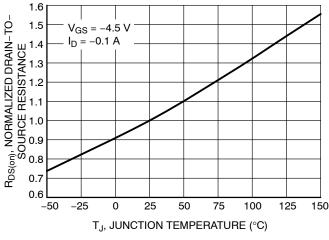


Figure 5. On–Resistance Variation with Temperature

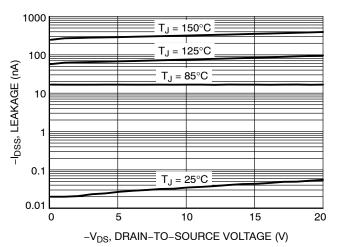


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

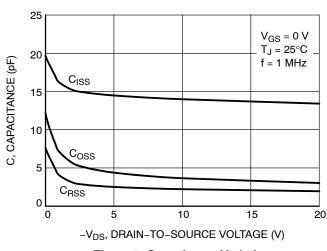


Figure 7. Capacitance Variation

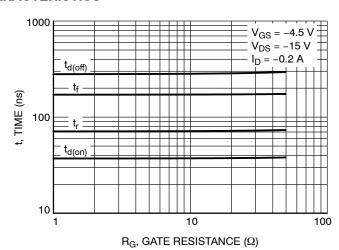


Figure 8. Resistive Switching Time Variation vs. Gate Resistance

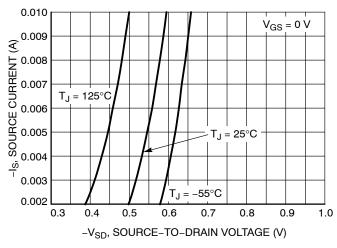


Figure 9. Diode Forward Voltage vs. Current

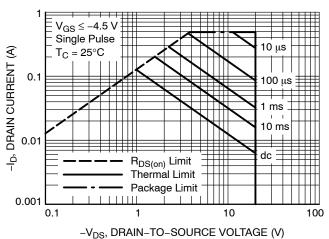


Figure 10. Maximum Rated Forward Biased Safe Operating Area

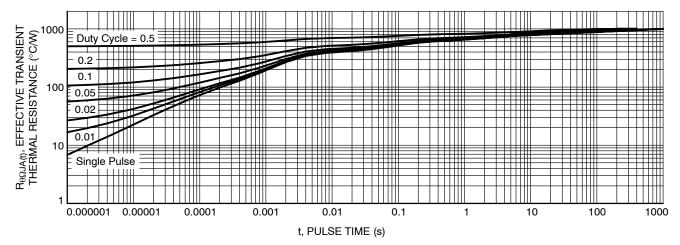
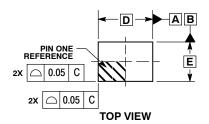


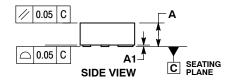
Figure 11. Thermal Response

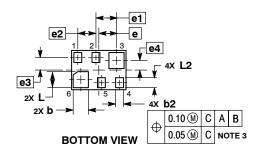


XLLGA6 0.90x0.65 CASE 713AC **ISSUE O**

DATE 19 JUN 2014







- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994 .
 CONTROLLING DIMENSION: MILLIMETERS.
- POSITIONAL TOERANCE APPLIES TO ALL SIX LEADS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.340	0.440		
A1	0.000	0.050		
b	0.200	0.300		
b2	0.080 0.180			
D	0.900 BSC			
Е	0.650 BSC			
е	0.295 BSC			
e1	0.340 BSC			
e2	0.300 BSC			
е3	0.208 BSC			
e4	0.158 BSC			
L	0.215	0.315		
L2	0.115	0.215		

GENERIC MARKING DIAGRAM*

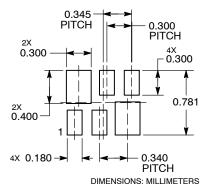


= Specific Device Code Х

= Date Code М

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	XLLGA6 0.90X0.65		PAGE 1 OF 1	

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